

Amendment to the Claims

Please amend claims 1 and 24 as follows:

- 1 (Currently Amended): A plasma immersion ion implant apparatus comprising:
 - a plasma chamber configured to receive a process gas;
 - a radio frequency (RF) source configured to resonate radio frequency currents in a radio frequency antenna;
 - a radio frequency antenna including an active antenna surrounding the plasma chamber and coupled to the RF source at a first end and coupled to ground at a second end and a parasitic antenna surrounding the plasma chamber to provide a parasitic effect, wherein the parasitic antenna is not directly coupled to any RF source; ~~and~~
 - a platen for holding a target and biasing the target with a negative voltage,
 - wherein electro-magnetic fields induced by the radio frequency currents are effective to pass into the plasma chamber and excite and ionize the process gas to generate plasma within the plasma chamber, the plasma comprising ions that are attracted to the target by the negative voltage, thereby implanting ions into the target; and ~~tuned by parasitic damping via the parasitic antenna.~~
 - a coil adjuster positioned in the parasitic antenna that adjusts a number of turns of the parasitic antenna for tuning the ionic plasma by parasitically damping.

- 2 (Original): The apparatus of claim 1, wherein the active antenna includes a horizontally-extending coil and the parasitic antenna includes a vertically-extending coil.
- 3 (Original): The apparatus of claim 1, wherein the active antenna includes a vertically-extending coil and the parasitic antenna includes a horizontally-extending coil.
- 4 (Original): The apparatus of claim 1, wherein the parasitic antenna includes a plurality of turns with one end grounded.
- 5 (Original): The apparatus of claim 4, further comprising means for adjusting a number of turns of the parasitic antenna providing a parasitic effect.
- 6 (Withdrawn): The apparatus of claim 1, wherein the parasitic antenna includes a plurality of turns with both ends floating.
- 7 (Original): The apparatus of claim 1, wherein an inner diameter of each antenna is greater than a size of the target.
- 8 (Original): The apparatus of claim 1, wherein the parasitic antenna is above and coaxial with the active antenna.
- 9 (Original): The apparatus of claim 1, wherein at least one antenna is liquid cooled.
- 10 Cancelled.
- 11 (Original): The apparatus of claim 1, wherein the plasma chamber includes:
a horizontal planar section positioned above the platen;

a vertical cylindrical section extending from the horizontal planar section; and
a top section coupled to the vertical cylindrical section.

- 12 (Original): The apparatus of claim 11, wherein the horizontal planar section and vertical cylindrical section are dielectric, and the top section is conductive and grounded.
- 13 (Original): The apparatus of claim 12, wherein the horizontal planar section and vertical cylindrical section are formed of a high purity ceramic material.
- 14 (Original): The apparatus of claim 13, wherein the high purity ceramic material is >99.6% Al_2O_3 , AlN, Yittria or YAG.
- 15 (Original): The apparatus of claim 12, wherein the top section is formed of Al.
- 16 (Original): The apparatus of claim 11, wherein the top section is liquid cooled.
- 17 (Original): The apparatus of claim 1, further comprising a plasma igniter for introducing a strike gas into the plasma chamber to assist in igniting a plasma.
- 18 (Original): The apparatus of claim 1, further comprising a gas source controller for maintaining a pressure of the plasma chamber at a predetermined value.
- 19 (Original): The apparatus of claim 1, wherein the RF source operates at a low RF frequency.
- 20 (Original): The apparatus of claim 19, wherein the low RF frequency is less than 27 MHz.

- 21 (Original): The apparatus of claim 19, wherein the low RF frequency is 400 KHz, 2 MHz, 4 MHz or 13.56 Mhz.
- 22 (Withdrawn): A method of plasma immersion ion implantation, the method comprising the steps of:
generating an ionic plasma by exposing a process gas to a radio frequency (RF) source via a first active coil;
tuning the ionic plasma by parasitically damping via a second parasitic coil that is not connected to any RF source; and
implanting a target using the ionic plasma by providing a negative voltage to the target.
- 23 (Withdrawn): The method of claim 22, wherein the generating step further includes introducing a strike gas to the RF source.
- 24 (Currently Amended): A plasma chamber comprising:
a horizontal planar dielectric section for positioning above a platen;
a vertical cylindrical dielectric section extending from the horizontal planar section;
a liquid cooled top conductive section coupled to the vertical dielectric section;
~~and~~
a radio frequency antenna including a horizontally-extending coil positioned proximate to the horizontal planar dielectric section and a vertically-extending coil positioned proximate to the vertical cylindrical dielectric section,

wherein one of the horizontally-extending coil and the vertically-extending coil comprises a parasitic antenna, the radio frequency antenna inducing radio frequency currents into the plasma chamber that excite and ionize a process gas so as to generate a plasma in the plasma chamber ~~that is tuned by parasitic damping via the parasitic antenna; and~~
a coil adjuster positioned in the parasitic antenna that adjusts a number of turns of the parasitic antenna for tuning the ionic plasma by parasitically damping.

25 (Original): The plasma chamber of claim 24, wherein the top conductive section is grounded.

26 Canceled.

27 (Previously Presented): The plasma chamber of claim 24, wherein the vertically-extending coil comprises a parasitic antenna that is not coupled to any radio frequency (RF) source.

28 (Original): The plasma chamber of claim 27, wherein the parasitic antenna includes a plurality of turns with one end grounded.

29 (Original): The plasma chamber of claim 28, further comprising means for adjusting a number of turns of the parasitic antenna providing a parasitic effect.

30 (Previously Presented): The plasma chamber of claim 24, wherein the radio frequency antenna is liquid cooled.

- 31 (Previously Presented): The plasma chamber of claim 24, wherein the horizontally-extending coil an active radio frequency antenna that is coupled to a radio frequency (RF) source.
- 32 (Original): The plasma chamber of claim 24, further comprising a process gas inlet and a strike gas inlet.

REMARKS

Interview Summary

The Applicants and the Applicant's attorney thank the Examiner for the telephone interview on October 9, 2007. In the interview the parasitic antenna claimed in the pending claims was discussed in detail. Also, the primary references, Kadomura and Okumura were discussed in detail. Several proposed claim amendments to claim 1 were discussed including amendments to recite that one end of the active antenna is coupled to ground, the position of the parasitic antenna, and the addition of a coil adjuster. Also, amendments to recite structural limitations that require the apparatus to implant ions into the target were discussed. The present Amendment and Response includes these proposed claim amendments.

If the present Amendment and Response does not overcome the pending rejections, the Applicants and the Applicant's attorney hereby request an interview with the Applicant's Attorney and with Dr. Vikram Singh. In particular, the Applicants request an interview to discuss why the prior art of record does not describe the claimed parasitic antennas. In addition, Applicants request an interview to discuss why the prior